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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wu et al.

Art Unit: 2818

Serial No.: 10/697,510

Examiner: Ho, T.

Filing Date: 10/30/2003

Docket No.: TI-36311

Customer No.: 23494

Conf. No.: 7656

Title: PROCESS TO REDUCE GATE EDGE DRAIN LEAKAGE IN
SEMICONDUCTOR DEVICES

ELECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

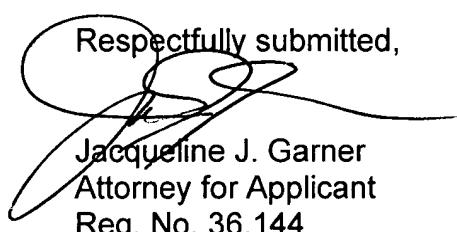
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I hereby certify that the above correspondence is being deposited with the U.S. Postal Service as first Class Mail in an envelope addressed to Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450.

9-16-04
Date
Marianna Smith
Marianna Smith

Dear Sir:

With respect to the Restriction Requirement mailed on 08/31/2004, the Examiner has restricted the instant application to the invention of Group I (Claims 1-9), or Group II (Claims 10-25). In light of this, Applicants elect to pursue Group I, (Claims 1-9) without traverse.

Respectfully submitted,


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